



UCBD20120SA

SiC-SBD DIODE

SILICON CARBIDE SCHOTTKY BARRIER DIODES

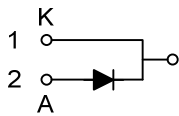
DESCRIPTION

The **UCBD20120SA** is an SiC Schottky barrier diodes (SBDs) feature high reverse voltage ratings. In addition to SBDs with short reverse recovery time (t_{rr}), provides 1200V SBDs with a junction barrier Schottky (JBS) structure that provide low leakage current (I_r) and high surge current capability required for switched-mode power supplies. These devices help improve the efficiency of switched-mode power supplies.

FEATURES

- * Zero Reverse Recovery Current
- * Humidity Resistant
- * High Frequency Operation
- * Temperature-Independent Switching Behavior

SYMBOL



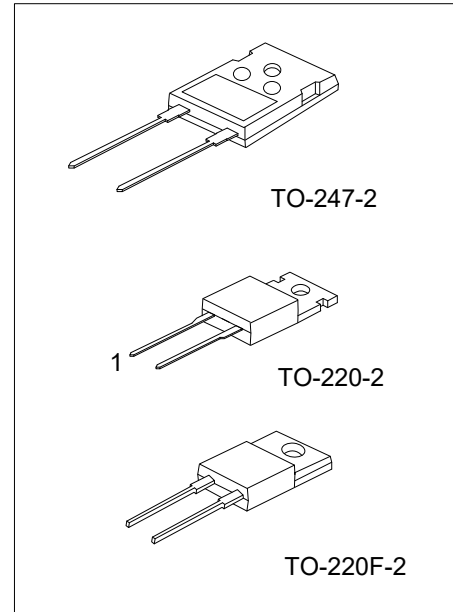
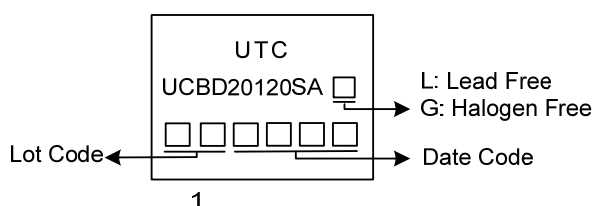
ORDERING INFORMATION

| Ordering Number | | Package | Pin Assignment | | Packing |
|---------------------|---------------------|-----------|----------------|---|---------|
| Lead Free | Halogen Free | | 1 | 2 | |
| UCBD20120SAL-TA2-T | UCBD20120SAG-TA2-T | TO-220-2 | K | A | Tube |
| UCBD20120SAL-TF32-T | UCBD20120SAG-TF32-T | TO-220F-2 | K | A | Tube |
| UCBD20120SAL-T472-T | UCBD20120SAG-T472-T | TO-247-2 | K | A | Tube |

Note: Pin Assignment: K: Cathode A: Anode

| | |
|--|---|
| <p>UCBD20120SAG-TA2-T</p> <p>(1) Packing Type (2) Package Type (3) Green Package</p> | <p>(1) T: Tube (2) TA2: TO-220-2, TF32: TO-220F-2, T472: TO-247-2 (3) G: Halogen Free and Lead Free, L: Lead Free</p> |
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MARKING



■ ABSOLUTE MAXIMUM RATINGS ($T_C=25^{\circ}\text{C}$, unless otherwise specified)

Ratings at 25°C ambient temperature unless otherwise specified. Resistive or inductive load, 60Hz.

| PARAMETER | | SYMBOL | RATINGS | UNIT |
|---|--|-----------|-----------------|--------------------|
| Repetitive Peak Reverse Voltage | | V_{RRM} | 1200 | V |
| Surge Peak Reverse Voltage | | V_{RSM} | 1200 | V |
| DC Blocking Voltage | | V_R | 1200 | V |
| Continuous Forward Current | $T_C=25^{\circ}\text{C}$ | I_F | 52 | A |
| | $T_C=135^{\circ}\text{C}$ | | 27 | A |
| | $T_C=152^{\circ}\text{C}$ | | 20 | A |
| Repetitive Peak Forward Surge Current | $T_J=25^{\circ}\text{C}$ $t_p=10\text{ms}$, Half Sine Wave | I_{FRM} | 162 | A |
| Non-Repetitive Peak Forward Surge Current | $T_J=25^{\circ}\text{C}$ $t_p=10\text{ms}$, Half Sine Wave | I_{FSM} | 181 | A |
| | $T_J=110^{\circ}\text{C}$ $t_p=10\text{ms}$, Half Sine Wave | | 172 | A |
| Power Dissipation | TO-220-2 | P_D | 200 | W |
| | TO-220F-2 | | 167 | W |
| | TO-247-2 | | 217 | W |
| Operating Junction Temperature | | T_J | $-55 \sim +175$ | $^{\circ}\text{C}$ |
| Storage Temperature Range | | T_{STG} | $-55 \sim +175$ | $^{\circ}\text{C}$ |

Note: Absolute maximum ratings are those values beyond which the device could be permanently damaged.
Absolute maximum ratings are stress ratings only and functional device operation is not implied.

■ THERMAL DATA

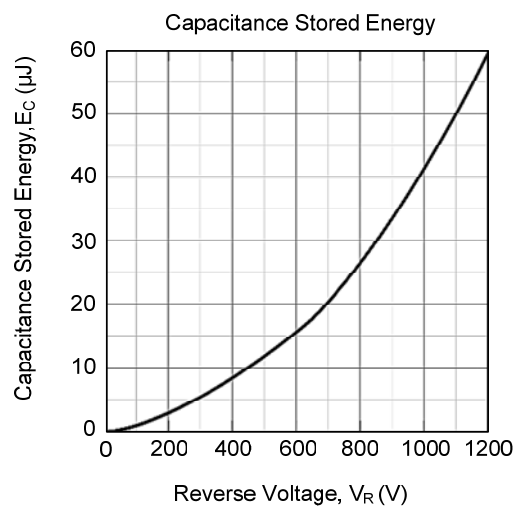
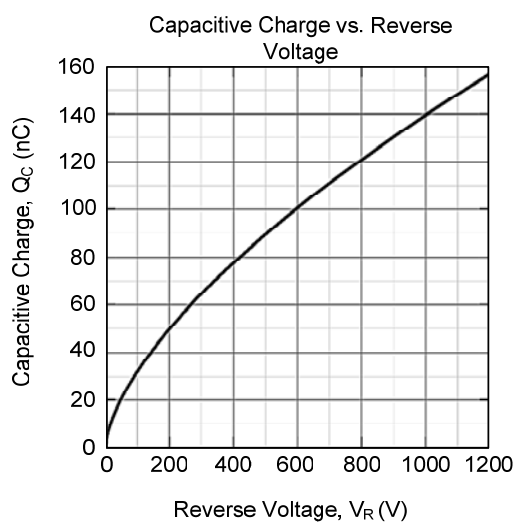
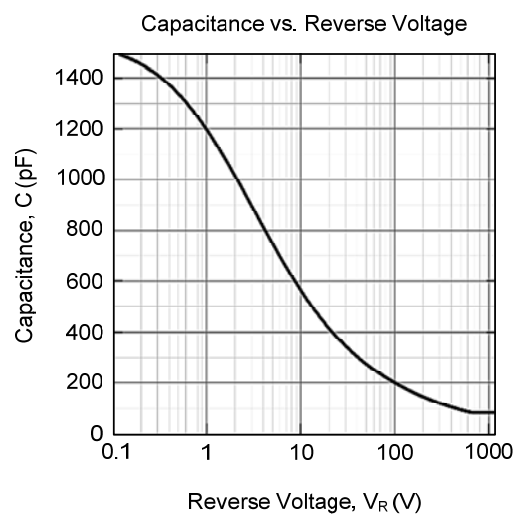
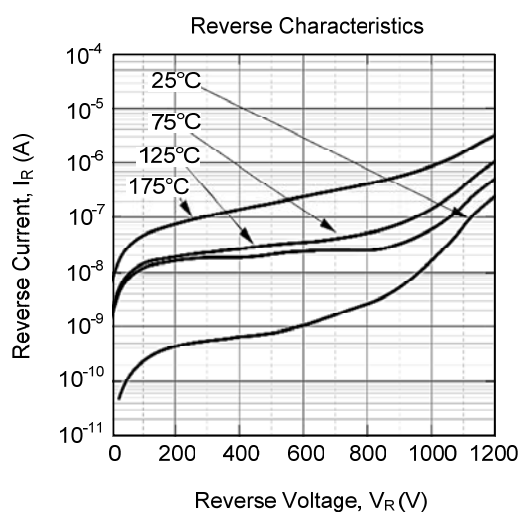
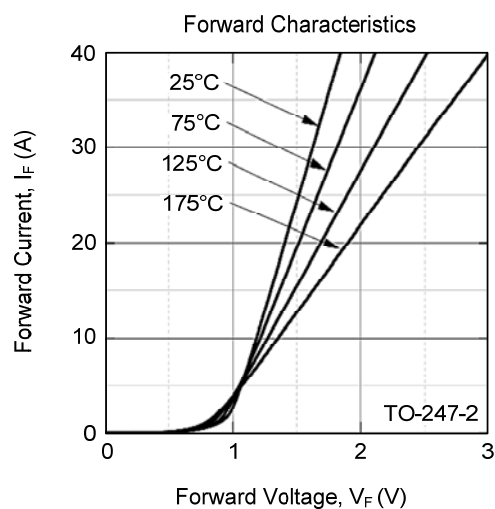
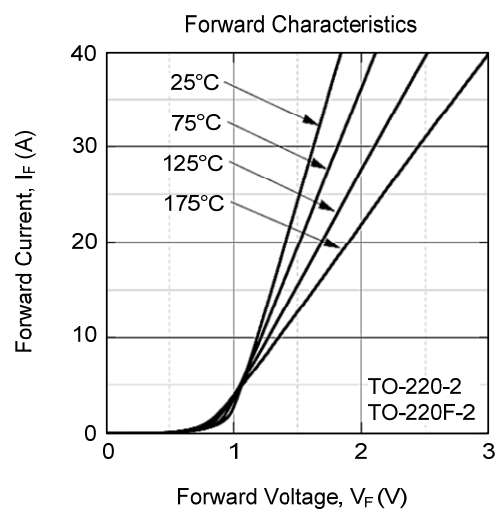
| PARAMETER | | SYMBOL | RATINGS | UNIT |
|------------------|-----------|---------------|---------|----------------------|
| Junction to Case | TO-220-2 | θ_{JC} | 0.75 | $^{\circ}\text{C/W}$ |
| | TO-220F-2 | | 0.9 | $^{\circ}\text{C/W}$ |
| | TO-247-2 | | 0.69 | $^{\circ}\text{C/W}$ |

■ ELECTRICAL CHARACTERISTICS

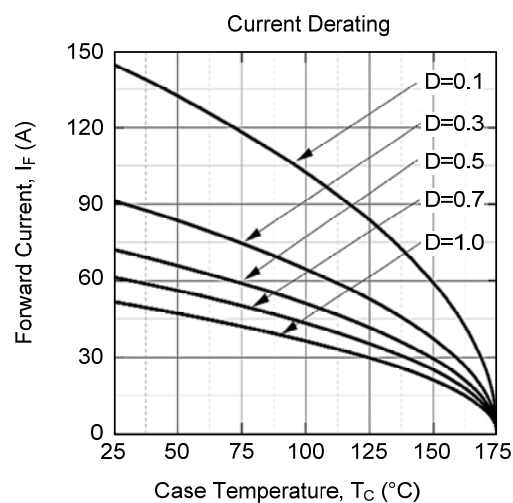
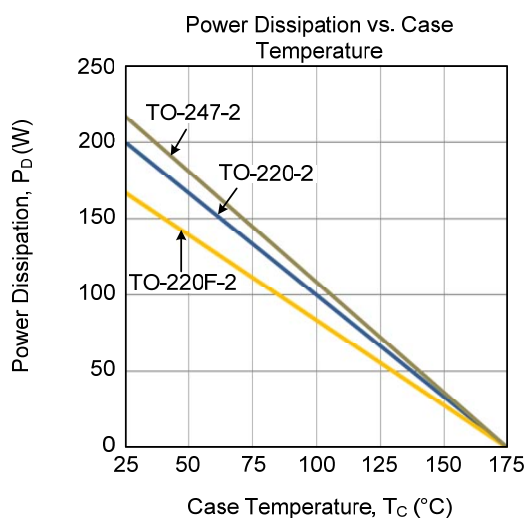
(Ratings at 25°C ambient temperature unless otherwise specified. Resistive or inductive load, 60Hz)

| PARAMETER | | SYMBOL | TEST CONDITIONS | MIN | TYP | MAX | UNIT |
|---------------------------|-----------|----------|-------------------------------|------|------|------|---------|
| DC Blocking Voltage | | V_{DC} | $T_C=25^{\circ}C$ | 1200 | | | V |
| Forward Voltage | TO-220-2 | V_F | $I_F=10A, T_J=25^{\circ}C$ | | 1.19 | | V |
| | TO-220F-2 | | | | | | |
| | TO-247-2 | | | | | | |
| | TO-220-2 | | $I_F=20A, T_J=25^{\circ}C$ | | 1.41 | 1.60 | V |
| | TO-220F-2 | | | | 1.41 | 1.65 | V |
| | TO-247-2 | | | | 1.40 | 1.60 | V |
| | TO-220-2 | | $I_F=20A, T_J=175^{\circ}C$ | | 1.68 | | V |
| | TO-220F-2 | | | | | | |
| | TO-247-2 | | | | 1.67 | | V |
| Reverse Current | | I_R | $V_R=1200V, T_J=25^{\circ}C$ | | 1.0 | 100 | μA |
| | | | $V_R=1200V, T_J=175^{\circ}C$ | | 10 | | μA |
| Total Capacitive Charge | | Q_C | $V_R=800V$ | | 120 | | nC |
| Total Capacitance | | C | $V_R=1.0V, f=1MHz$ | | 1193 | | pF |
| | | | $V_R=400V, f=1MHz$ | | 104 | | pF |
| | | | $V_R=800V, f=1MHz$ | | 83 | | pF |
| Capacitance Stored Energy | | E_C | $V_R=800V$ | | 26 | | μJ |

TYPICAL CHARACTERISTICS



■ TYPICAL CHARACTERISTICS (Cont.)



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